# 1.3 Watt Audio Power Amplifier with Fast Turn On Time

The NCP2990 is an audio power amplifier designed for portable communication device applications such as mobile phone applications. The NCP2990 is capable of delivering 1.3 W of continuous average power to an  $8.0~\Omega$  BTL load from a 5.0~V power supply, and 1.0~W to a  $4.0~\Omega$  BTL load from a 3.6~V power supply.

The NCP2990 provides high quality audio while requiring few external components and minimal power consumption. It features a low–power consumption shutdown mode, which is achieved by driving the SHUTDOWN pin with logic low.

The NCP2990 contains circuitry to prevent from "pop and click" noise that would otherwise occur during turn—on and turn—off transitions. It is a zero pop noise device when a single ended audio input is used.

For maximum flexibility, the NCP2990 provides an externally controlled gain (with resistors), as well as an externally controlled turn—on time (with the bypass capacitor). When using a 1  $\mu$ F bypass capacitor, it offers 60 ms wake up time.

Due to its superior PSRR, it can be directly connected to the battery, saving the use of an LDO.

This device is available in a 9-Pin Flip-Chip CSP (Lead-Free).

### **Features**

- 1.3 W to an 8.0 Ω BTL Load from a 5.0 V Power Supply
- Superior PSRR: Direct Connection to the Battery
- Zero Pop Noise Signature with a Single Ended Audio Input
- Ultra Low Current Shutdown Mode: 10 nA
- 2.2 V-5.5 V Operation
- External Gain Configuration Capability
- External Turn–on Time Configuration Capability: 60 ms (1 µF Bypass Capacitor)
- Up to 1.0 nF Capacitive Load Driving Capability
- Thermal Overload Protection Circuitry
- This is a Pb-Free Device\*

# **Typical Applications**

- Portable Electronic Devices
- PDAs
- Wireless Phones



# ON Semiconductor®

http://onsemi.com

### MARKING DIAGRAMS



9-Pin Flip-Chip CSP FC SUFFIX CASE 499E



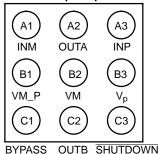
MBA = Specific Device Code A = Assembly Location

= Year

WW = Work Week ■ Pb–Free Package

#### **PIN CONNECTIONS**

9-Pin Flip-Chip CSP



(Tan Minus)

(Top View)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

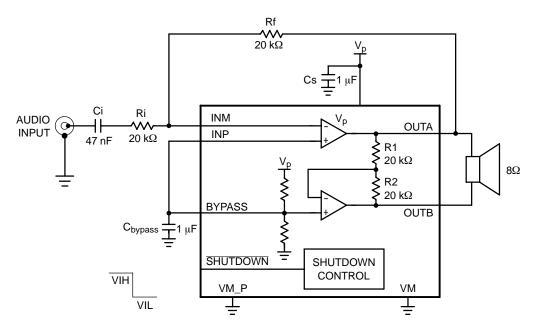


Figure 1. Typical Audio Amplifier Application Circuit with Single Ended Input

#### **PIN DESCRIPTION**

Pin	Type	Symbol	Description
A1	I	INM	Negative input of the first amplifier, receives the audio input signal. Connected to the feedback resistor $R_{\rm f}$ and to the input resistor $R_{\rm in}$ .
A2	0	OUTA	Negative output of the NCP2990. Connected to the load and to the feedback resistor Rf.
А3	I	INP	Positive input of the first amplifier, receives the common mode voltage.
B1	I	VM_P	Power Analog Ground.
B2	1	VM	Core Analog Ground.
В3	1	V <sub>p</sub>	Positive analog supply of the cell. Range: 2.2 V-5.5 V.
C1	1	BYPASS	Bypass capacitor pin which provides the common mode voltage (Vp/2).
C2	0	OUTB	Positive output of the NCP2990. Connected to the load.
C3	I	SHUTDOWN	The device enters in shutdown mode when a low level is applied on this pin.

### MAXIMUM RATINGS (Note 1)

Rating		Symbol	Value	Unit	
Supply Voltage		V <sub>p</sub>	6.0	V	
Operating Supply Voltage		Op Vp	2.2 to 5.5 V 2.0 V = Functional Only	-	
Input Voltage		V <sub>in</sub>	-0.3 to Vcc +0.3	V	
Max Output Current		lout	500	mA	
Power Dissipation (Note 2)		Pd	Internally Limited	-	
Operating Ambient Temperature		T <sub>A</sub>	-40 to +85	°C	
Max Junction Temperature		TJ	150	°C	
Storage Temperature Range		T <sub>stg</sub>	-65 to +150	°C	
Thermal Resistance Junction-to-Air		$R_{\theta JA}$	(Note 3)	°C/W	
•	Model (HBM) (Note 4) Model (MM) (Note 5)	_	8000 >250	V	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. Maximum electrical ratings are defined as those values beyond which damage to the device may occur at T<sub>A</sub> = +25°C.
- The thermal shutdown set to 160°C (typical) avoids irreversible damage on the device due to power dissipation.
   The R<sub>BJA</sub> is highly dependent of the PCB Heatsink area. For example, R<sub>BJA</sub> can equal 195°C/W with 50 mm² total area and also 135°C/W with 500 mm². For further information see page 10. The bumps have the same thermal resistance and all need to be connected to optimize the power
- 4. Human Body Model, 100 pF discharge through a 1.5 kΩ resistor following specification JESD22/A114.
- 5. Machine Model, 200 pF discharged through all pins following specification JESD22/A115.

# **ELECTRICAL CHARACTERISTICS** Limits apply for $T_A$ between $-40^{\circ}$ C to $+85^{\circ}$ C (Unless otherwise noted).

Characteristic	Symbol	Conditions	Min (Note 6)	Тур	Max (Note 6)	Unit
Supply Quiescent Current	I <sub>dd</sub>	$V_p = 2.6 \text{ V}$ , No Load $V_p = 5.0 \text{ V}$ , No Load	_ _	1.5 1.7	4	mA
		$V_p = 2.6 \text{ V}, 8 \Omega$ $V_p = 5.0 \text{ V}, 8 \Omega$	_ _	1.7 1.9	5.5	
Common Mode Voltage	V <sub>cm</sub>	_	-	V <sub>p</sub> /2	_	V
Shutdown Current	I <sub>SD</sub>		-	0.02	0.3	μΑ
Shutdown Voltage High	V <sub>SDIH</sub>	_	1.2	_	_	V
Shutdown Voltage Low	V <sub>SDIL</sub>	-	_	_	0.4	V
Turning On Time (Note 8)	T <sub>WU</sub>	$C_{by} = 1 \mu F$	-	60	_	ms
Turning Off Time	T <sub>OFF</sub>	-	-	1.0	_	μS
Output Impedance in Shutdown Mode	Z <sub>SD</sub>	-	_	10	-	kΩ
Output Swing	V <sub>loadpeak</sub>	$V_p = 2.6 \text{ V}, R_L = 8.0 \Omega$ $V_p = 5.0 \text{ V}, R_L = 8.0 \Omega \text{ (Note 7)}$ $T_A = +25^{\circ}\text{C}$	1.6 4.0	2.20 4.50	_ _	V
		$T_A = -40^{\circ}C$ to +85°C	3.85			
Rms Output Power	P <sub>O</sub>	$V_p = 2.6 \text{ V}, R_L = 4.0 \Omega$ THD + N < 0.1%	-	0.40	_	W
		$V_p$ = 2.6 V, R <sub>L</sub> = 8.0 $\Omega$ THD + N < 0.1% $V_p$ = 5.0 V, R <sub>L</sub> = 8.0 $\Omega$ THD + N < 0.1%	_	0.30 1.20	-	
Maximum Power Dissipation (Note 8)	P <sub>Dmax</sub>	$V_p = 5.0 \text{ V}, R_L = 8.0 \Omega$	_	_	0.65	W
Output Offset Voltage	V <sub>OS</sub>	$V_p = 3.0 \text{ V},  N_L = 6.0 \text{ Sz}$ $V_p = 2.6 \text{ V}$	-30		30	mV
Output Offset Voltage	VOS	$V_p = 2.0 \text{ V}$ $V_p = 5.0 \text{ V}$	-30		30	IIIV
Signal-to-Noise Ratio	SNR	$V_p = 2.6 \text{ V}, G = 2.0$	-	84	_	dB
		10 Hz < F < 20 kHz $V_p = 5.0 V, G = 10$ 10 Hz < F < 20 kHz	_	77	-	
Positive Supply Rejection Ratio	PSRR V+	$G=2.0,\ R_L=8.0\ \Omega$ $Vp_{ripple\_pp}=200\ mV$ $C_{by}=1.0\ \mu F$ Input Terminated with 10 $\Omega$ $F=217\ Hz$ $V_p=4.2\ V$ $V_p=3.6\ V$ $V_p=3.0\ V$	- - -	-74 -72 -73	- - -	dB
		F = 1.0  kHz $V_p = 4.2 \text{ V}$ $V_p = 3.6 \text{ V}$ $V_p = 3.0 \text{ V}$	- - -	-80 -76 -77	- - -	
Efficiency	η	$V_p = 2.6 \text{ V}, \ P_{orms} = 320 \text{ mW}$ $V_p = 5.0 \text{ V}, \ P_{orms} = 1.0 \text{ W}$	_ _	48 63	- -	%
Thermal Shutdown Temperature (Note 9)	T <sub>sd</sub>		140	160	180	°C
Total Harmonic Distortion	THD	$V_p = 2.6, F = 1.0 \text{ kHz}$ $R_L = 4.0 \Omega, A_V = 2.0$ $P_O = 0.32 \text{ W}$	- - -	- 0.04 -	- - -	%
		$V_p = 5.0 \text{ V}, F = 1.0 \text{ kHz}$ $R_L = 8.0 \Omega, A_V = 2.0$ $P_O = 1.0 \text{ W}$	- - -	- 0.02 -	- - -	

<sup>6.</sup> Min/Max limits are guaranteed by design, test or statistical analysis.
7. This parameter is guaranteed but not tested in production in case of a 5.0 V power supply.
8. See page 9 for a theoretical approach of this parameter.
9. For this parameter, the Min/Max values are given for information.

#### TYPICAL PERFORMANCE CHARACTERISTICS

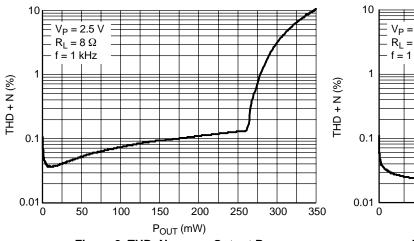


Figure 2. THD+N versus Output Power

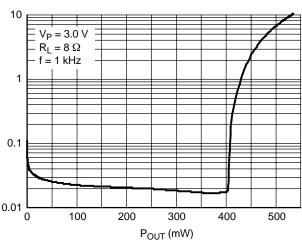


Figure 3. THD+N versus Output Power

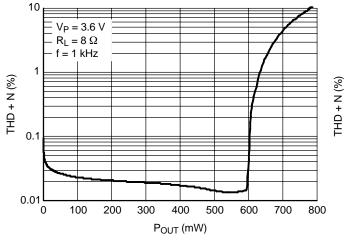


Figure 4. THD+N versus Output Power

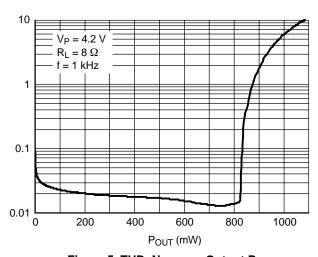


Figure 5. THD+N versus Output Power

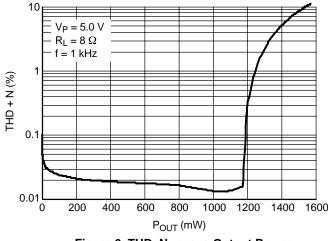


Figure 6. THD+N versus Output Power

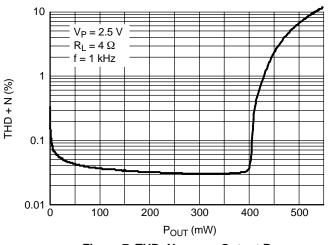


Figure 7. THD+N versus Output Power

#### TYPICAL PERFORMANCE CHARACTERISTICS

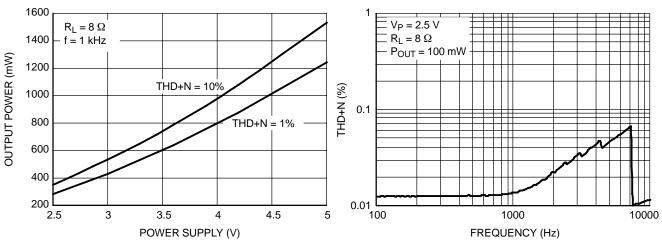


Figure 8. Output Power versus Power Supply

Figure 9. THD+N versus Frequency

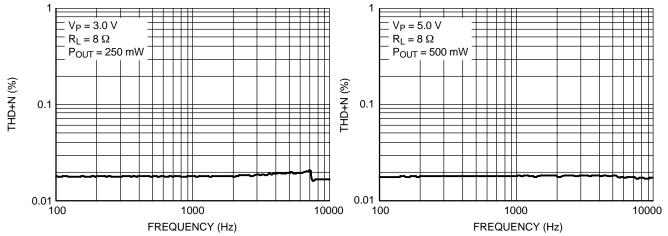


Figure 10. THD+N versus Frequency

Figure 11. THD+N versus Frequency

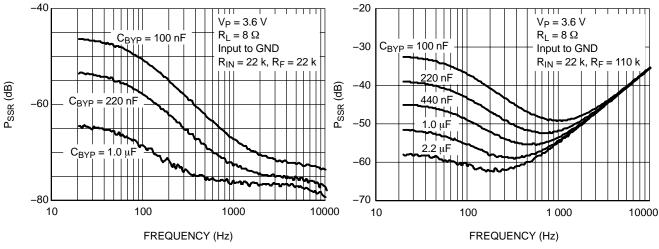


Figure 12.  $P_{SRR}$  versus Frequency and  $C_{BYP} @ V_P = 3.6 \text{ V}, A_V = 2$ 

Figure 13.  $P_{SRR}$  versus Frequency and  $C_{BYP}$ @  $V_P = 3.6$  V,  $A_V = 10$ 

#### TYPICAL PERFORMANCE CHARACTERISTICS

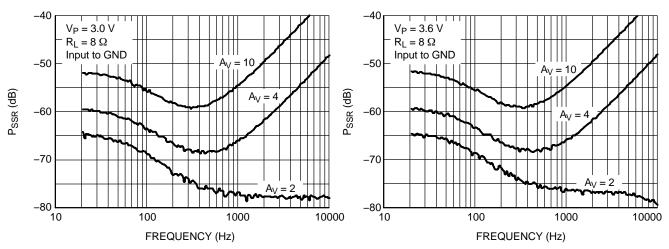


Figure 14.  $P_{SRR}$  versus Frequency and Gain @  $V_P = 3.0 \text{ V}$ 

Figure 15.  $P_{SRR}$  versus Frequency and Gain @  $V_P = 3.6 \text{ V}$ 

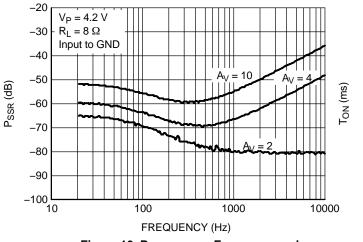
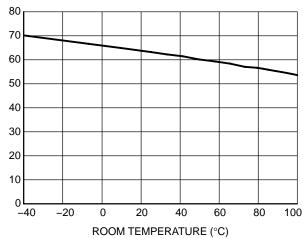


Figure 16.  $P_{SRR}$  versus Frequency and Gain @  $V_P = 4.2 \text{ V}$ 



 $\label{eq:figure 17.7} Figure 17. Turn On Time versus \\ Room Temperature @ V_{BAT} = 3.6 \ V, \\ C_{BYP} = 1 \ \mu F, C_{IN} = 100 \ nF, R_{IN} = 22 \ k, R_F = 110 \ k$ 

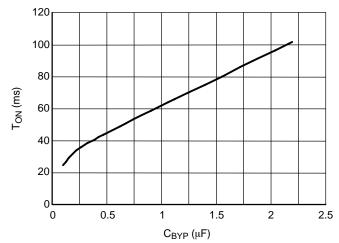


Figure 18. Turn On Time versus  $C_{BYP}$  @  $V_{BAT}$  = 3.6 V,  $T_A$  = +25°C,  $C_{IN}$  = 100 nF,  $R_{IN}$  = 22 k,  $R_F$  = 110 k

#### TYPICAL PERFORMANCE CHARACTERISTICS

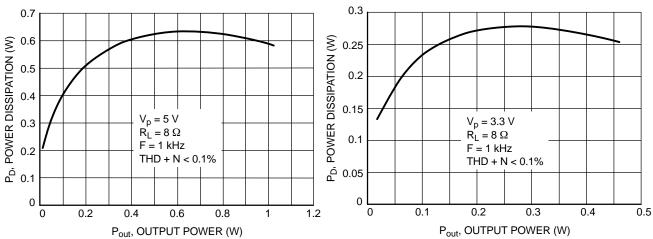


Figure 19. Power Dissipation versus Output
Power

Figure 20. Power Dissipation versus Output Power

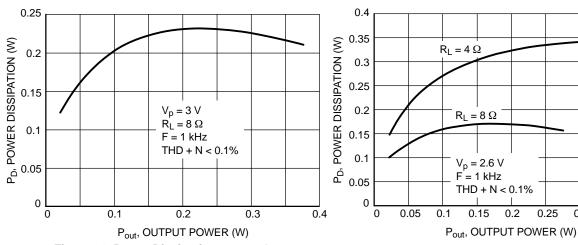


Figure 21. Power Dissipation versus Output
Power

Figure 22. Power Dissipation versus Output

0.3

0.35

0.4

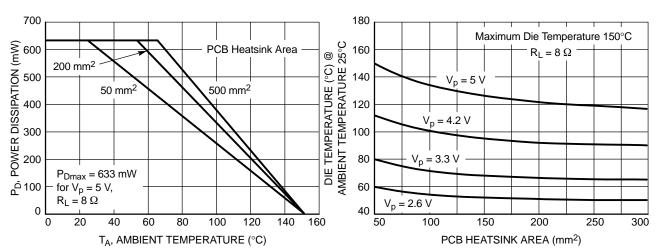


Figure 23. Power Derating - 9-Pin Flip-Chip CSP

Figure 24. Maximum Die Temperature versus PCB Heatsink Area

#### APPLICATION INFORMATION

#### **Detailed Description**

The NCP2990 audio amplifier can operate under 2.6 V until 5.5 V power supply. With less than 1% THD + N, it can deliver up to 1.2 W RMS output power to an 8.0  $\Omega$  load (V<sub>P</sub> = 5.0 V). If application allows to reach 10% THD + N, then 1.6 W can be provided using a 5.0 V power supply.

The structure of the NCP2990 is basically composed of two identical internal power amplifiers; the first one is externally configurable with gain–setting resistors  $R_{in}$  and  $R_f$  (the closed–loop gain is fixed by the ratios of these resistors) and the second is internally fixed in an inverting unity–gain configuration by two resistors of 20 k $\Omega$ . So the load is driven differentially through OUTA and OUTB outputs. This configuration eliminates the need for an output coupling capacitor.

#### **Internal Power Amplifier**

The output PMOS and NMOS transistors of the amplifier were designed to deliver the output power of the specifications without clipping. The channel resistance ( $R_{on}$ ) of the NMOS and PMOS transistors does not exceed 0.6  $\Omega$  when they drive current.

The structure of the internal power amplifier is composed of three symmetrical gain stages, first and medium gain stages are transconductance gain stages to obtain maximum bandwidth and DC gain.

#### Turn-On and Turn-Off Transitions

A cycle with a turn-on and turn-off transition is illustrated with plots that show both single ended signals on the previous page.

In order to eliminate "pop and click" noises during transitions, output power in the load must be slowly established or cut. When logic high is applied to the shutdown pin, the bypass voltage begins to rise exponentially and once the output DC level is around the common mode voltage, the gain is established instantaneously. This way to turn—on the device is optimized in terms of rejection of "pop and click" noises.

The device has the same behavior when it is turned–off by a logic low on the shutdown pin. During the shutdown mode, amplifier outputs are connected to the ground using a 10  $k\Omega$  pulldown resistor.

When a shutdown low level is applied, with 1  $\mu$ F bypass capacitor, it takes 65 ms before the DC output level is tied to Ground on each output. However, no audio signal will be provided to the BTL load instantaneously after the falling edge on the shutdown pin.

With  $1 \mu F$  bypass capacitor, turn on time is set to 60 ms. Refer to Figures 17 and 18 for a complete study of this parameter. This fast turn on time added to a very low shutdown current saves battery life and brings flexibility when designing the audio section of the final application.

NCP2990 is a zero pop noise device when using a single-ended audio input.

#### **Shutdown Function**

The device enters shutdown mode when shutdown signal is low. During the shutdown mode, the DC quiescent current of the circuit does not exceed 100 nA. In this configuration, the output impedance is 10 k $\Omega$  on each output.

#### **Current Limit Circuit**

The maximum output power of the circuit (Porms =  $1.0~W,~V_p = 5.0~V,~R_L = 8.0~\Omega$ ) requires a peak current in the load of 500 mA.

In order to limit the excessive power dissipation in the load when a short-circuit occurs, the current limit in the load is fixed to 800 mA. The current in the four output MOS transistors are real-time controlled, and when one current exceeds 800 mA, the gate voltage of the MOS transistor is clipped and no more current can be delivered.

#### **Thermal Overload Protection**

Internal amplifiers are switched off when the temperature exceeds 160°C, and will be switched on again only when the temperature decreases fewer than 140°C.

The NCP2990 is unity-gain stable and requires no external components besides gain-setting resistors, an input coupling capacitor and a proper bypassing capacitor in the typical application.

The first amplifier is externally configurable ( $R_f$  and  $R_{in}$ ), while the second is fixed in an inverting unity gain configuration.

The differential-ended amplifier presents two major advantages:

- The possible output power is four times larger (the output swing is doubled) as compared to a single-ended amplifier under the same conditions.
- Output pins (OUTA and OUTB) are biased at the same potential V<sub>p</sub>/2, this eliminates the need for an output coupling capacitor required with a single-ended amplifier configuration.

The differential closed loop-gain of the amplifier is given by  $A_{Vd} = 2 * \frac{Rf}{Rin} = \frac{V_{orms}}{V_{inrms}}$ . Output power delivered to the load is given by

Output power delivered to the load is given by  $P_{orms} = \frac{(Vopeak)^2}{2 R_L}$  (Vopeak is the peak differential output voltage).

When choosing gain configuration to obtain the desired output power, check that the amplifier is not current limited or clipped.

The maximum current which can be delivered to the load is 500 mA  $I_{opeak} = \frac{V_{opeak}}{RL}$ .

### Gain-Setting Resistor Selection (Rin and Rf)

 $R_{in}$  and  $R_f$  set the closed–loop gain of the amplifier. In order to optimize device and system performance, the NCP2990 should be used in low gain configurations.

The low gain configuration minimizes THD + noise values and maximizes the signal to noise ratio, and the amplifier can still be used without running into the bandwidth limitations.

A closed loop gain in the range from 2 to 5 is recommended to optimize overall system performance.

An input resistor ( $R_{in}$ ) value of 22 k $\Omega$  is realistic in most of applications, and doesn't require the use of a too large capacitor  $C_{in}$ .

# Input Capacitor Selection (Cin)

The input coupling capacitor blocks the DC voltage at the amplifier input terminal. This capacitor creates a high–pass filter with  $R_{in},$  the cut–off frequency is given by fc =  $\frac{1}{2^*\Pi^*R_{in}^*C_{in}}$  .

The size of the capacitor must be large enough to couple in low frequencies without severe attenuation.

An input capacitor value between 33 nF and 220 nF performs well in many applications (With  $R_{in} = 22 \text{ K}\Omega$ ).

#### **Bypass Capacitor Selection (Cby)**

The bypass capacitor Cby provides half—supply filtering and determines how fast the NCP2990 turns on. With a single—ended audio input, the amplifier will be a zero pop noise device no matter the bypass capacitor.

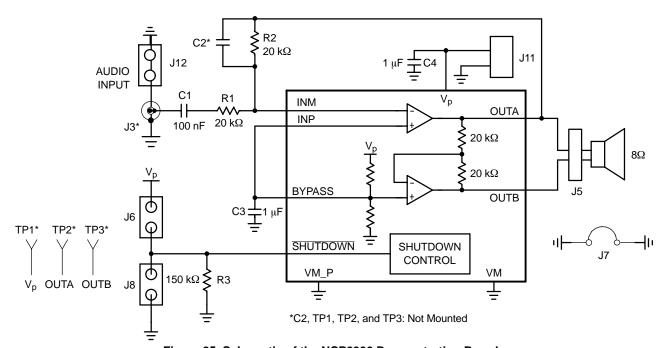


Figure 25. Schematic of the NCP2990 Demonstration Board

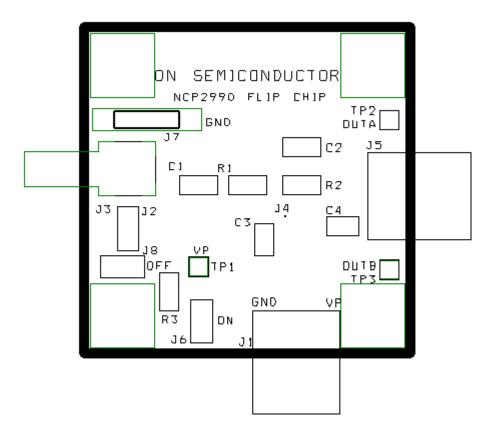


Figure 26. Demonstration Board for 9-Pin Flip-Chip CSP Device - Silkscreen Layers

### **BILL OF MATERIAL**

Item	Part Description	Ref.	PCB Footprint	Manufacturer	Manufacturer Reference
1	NCP2990 Audio Amplifier	-	_	ON Semiconductor	NCP2990
2	SMD Resistor 20 KΩ	R1, R2	0805	Panasonic	ERJ-6GEYJ203V
4	SMD Resistor 150 KΩ	R3	0805	Panasonic	ERJ-6GEYJ203V
5	Ceramic Capacitor 47 nF 100 V X7R	C1	0805	TDK	C2012X7R2A473K
6	Ceramic Capacitor 1.0 μF 10 V X7R	C3, C4	0805	TDK	C2012X7R1A105K
7	Jumper Header Vertical Mount, 2 positions, 100 mils	J2, J6, J18	100 mils	Tyco Electronics / AMP	5-826629-0
8	I/O Connector, 2 positions	J1, J5	200 mils	Phoenix Contact	1757242
9	Jumper Connector	J7	400 mils	Harwin	D3082-B01
10	Not Mounted	C2, TP1, TP2, TP3	-	-	-

# ORDERING INFORMATION

Device	Marking	Package	Shipping <sup>†</sup>
NCP2990FCT2G	MBA	9-Pin Flip-Chip CSP (Pb-Free)	3000/Tape and Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



#### 9 PIN FLIP-CHIP CASE 499E-01 **ISSUE A**



SCALE 4:1

Ø 0.03 C

**DATE 30 JUN 2004** 

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETERS.

  3. COPLANARITY APPLIES TO SPHERICAL CROWNS OF SOLDER BALLS.

	MILLIMETERS						
DIM	MIN	MAX					
Α	0.540	0.660					
A1	0.210	0.270					
A2	0.330	0.390					
D	1.450	BSC					
E	1.450	BSC					
b	0.290	0.340					
е	0.500 BSC						
D1	1.000 BSC						
E1	1.000 BSC						

### **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code = Assembly Location Α

Υ = Year WW = Work Week G or ■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

[	0.10 0.05 -C- SEATING PLANE	C 5 (	C	_	0	P VI	 A2	A A A A A A A A A A A A A A A A A A A	
	9 x Ø Ø 0.05	<b>b</b>	A E	- -		D1 → (1) → (2)	3	¥ É1	

**BOTTOM VIEW** 

DESCRIPTION:	9 PIN FLIP-CHIP, 1.45 X 1.	45 MM	PAGE 1 OF 1			
DOCUMENT NUMBER: 98AON12066D		Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.				

ON Semiconductor and at a trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative